## Claims

- 1."canceled".
- 2."currently amended". A transistor comprising elements of bipolar static induction transistors: [[two]] a gate, [[four]] sources and channels and six electrodes on either side of a lightly doped n-type silicon monocrystal substrate;
- one of said channel of the multielement structure is thicker than the other normally-off channels on either side of said substrate;
- said <u>thick channels are channel is</u> connected to a separate electrode on either side of said substrate.
  - 3."canceled".
- 4."currently amended". The transistor according to claim 2 wherein an epitaxial layers layer of the same type of conductivity with the impurity concentration of about 10.sup.17 cm.sup.-3 [[are]] is disposed on either side of said substrate;
- said [[gates]] gate, said sources and said channels are disposed in said epitaxial layers layer.
- 5."previously presented". The transistor according to claim 2 wherein a layer of a doped n+-type polysilicon is disposed on the silicon monocrystal surface.
- 6."currently amended". The transistor according to claim 2 wherein the control over both hole emission into and extraction out the lightly doped area are used as well as the current feedback for said control over emission into one.
- 7."previously presented". The transistor according to claim 2 wherein the thickness of said channels are small and the impurity concentration near said gates is high enough.
- 8."previously presented". The transistor according to claim 4 wherein a layer of a doped n+-type polysilicon is disposed on the silicon monocrystal surface.
- 9."currently amended". The transistor according to claim 4 wherein said thick channels are channel is normally-on [[ones]] one.

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